

V1.0 Datasheet

P-Channel 20V MOSFET

FEATURES

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

PRODUCTY SUMMARY				
V_{DS}	$R_{DS(on)} m(\Omega) Max$			
-20	9.3	@V _{GS} =-4.5V		
	11.4	@V _{GS} =-2.5V		

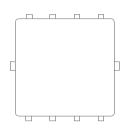
Application

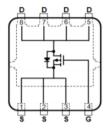
- Portable Devices
- ■Consumer Electronics

Mechanical

●Case:DFN3333 Package

DFN3333





Packing Information

Package	Packing		
DFN3333	5Kpcs/13"Reel		

Maximum Ratings (T _A =25°C unless otherwise specified)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V _{DS}	-20	V			
Gate-Source Voltage	V _{GS}	±12	V			
Continuous Drain Current 1)	I _D	-20	А			
Continuous Drain Current 4)	I _{DM}	-80	А			
Maximum Power Dissipation	P _D	5	W			
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C			

Typical Thermal Resistance						
Parameter	Symbol	Limit	Unit			
Junction-to-Ambient Thermal Resistance 3)	$R_{\theta JA}$	65	°C/W			

Note:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Fused current that based on wire numbers and diameter.
- 3. Guaranteed by design, not subject to production testing.
- 4. The maximum current rating is package limited.
- 5. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keepinitial T_J =25°C.

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Electrical Characteristics (T _A = 25°C UNLESS OTHERWISE NOTED)						
Characteristics	Symbol	Test Condition	Limits			1114
			Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	B _{VDSS}	V_{GS} =0V, I_D =-250uA	-20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-0.5	-0.7	-1.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-20A	-	7.9	9.3	mΩ
		V _{GS} =-2.5V, I _D =-20A	-	9.7	11.4	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V	-	-	1	uA
GateSource Leakage Current	I _{GSS}	V_{GS} =±12V, V_{DS} =0V	-	-	±100	nA
DrainSource Diode						
Maximum Continuous Body Diode Forward Current	Is	-	-	-	-1.2	А
Diode Forward Voltage	V_{SD}	I _S =-1.0A, V _{GS} =0V	-	-	-1.5	V

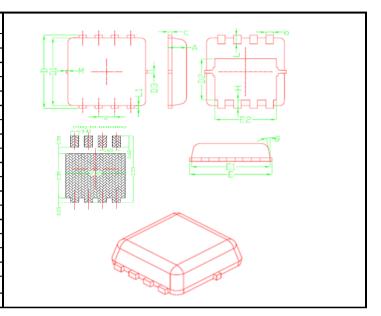
Note:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{QJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.

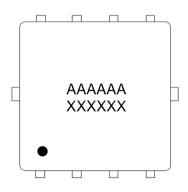


Package Outline Dimensions (inches and millimeters)

DFN3333					
	Dimensions				
SYMBOL	Millimeters		Inches		
	Min	Max	Min	Max	
Α	0.70	0.80	0.028	0.031	
b	0.25	0.35	0.010	0.014	
С	0.10	0.25	0.004	0.010	
D	3.25	3.45	0.128	0.136	
D1	3.00	3.20	0.118	0.126	
D2	1.78	1.98	0.070	0.078	
D3	-	0.13	-	0.005	
E	3.20	3.40	0.126	0.134	
E1	3.00	3.20	0.118	0.126	
E2	2.39	2.59	0.094	0.102	
е	0.65BSC				
Н	0.30	0.50	0.012	0.020	
L	0.30	0.50	0.012	0.020	
L1	0.13		-	0.005	
θ	-	12 °	-	12 °	
M	-	0.15	-	0.006	



Marking Information



AAAAAA = Product number

XXXXXX = Tracking number

Third line = Pin1 Point

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